

				Docket Number (Optional)		Application Number	
				FIS920030371US1		10/708, 378	
				Applicant(s)			
				Zhu, et al.			
				Filing Date		Group Art Unit	
2-27-04		2818					
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WJ		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
NN		4,952,524	8-28-90	Lee, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WJ		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
WJ		US 2002/0086472	7-4-02	Roberds, et al.			
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
NN	JP64-76755	03-1989	Japan				
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
WJ		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.					
NN		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.					
EXAMINER				DATE CONSIDERED 5-12-05			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) PIS920030371US1		Application Number 10/708,378	
				Applicant(s) Zhu, et al.			
				Filing Date 2-27-04		Group Art Unit 2818	
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>NP</i>		4,958,213	9-18-90	Eklund, et al.			
		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
<i>NP</i>		5,108,843	4-28-92	Ohtaka, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>NP</i>		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeh, et al.			
<i>NP</i>		US 2003/0040158 A1	2-27-03	Saitoh			
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>NP</i>		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress." International Electron Devices Meeting, 34.4.1, IEEE, September 1999.					
<i>NP</i>		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.					
EXAMINER <i>NP</i> ✓ M				DATE CONSIDERED 5-15-05			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M		5,134,085	7-28-92	Gilgen, et al.			
		5,310,446	5-10-94	Konishi, et al.			
		5,354,695	10-11-94	Leedy			
		5,371,399	12-6-94	Burroughes, et al.			
M		5,391,510	2-21-95	Hsu, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M		US 2003/0057184 A1	3-27-03	Yu, et al.			
M		US 2003/0067035 A1	4-10-03	Tews, et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

M Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and Its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.

M A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

EXAMINER	<i>M</i>	DATE CONSIDERED
		5-15-05

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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)	Application Number
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
W		5,565,697	10-15-96	Asakawa, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

W		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
W		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

EXAMINER		DATE CONSIDERED
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) PIS920030371US1		Application Number 10/708,378	
				Applicant(s) Zhu, et al.			
				Filing Date 2-27-04		Group Art Unit 2818	
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WJ		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
		5,679,965	10-21-97	Schetzina			
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATED YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
WJ		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.					
WJ		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.					
EXAMINER <i>WJ ✓ M</i>				DATE CONSIDERED <i>2-15-05</i>			
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		5,683,934	11-4-97	Candelaria			
1		5,840,593	11-24-98	Leedy			
1		5,861,651	1-19-99	Brasen, et al.			
1		5,880,040	3-9-99	Sun, et al.			
W		5,940,716	8-17-99	Jin, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Tide, Date, Pertinent Pages, Etc.)

W		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.
W		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.

EXAMINER	<i>W</i>	DATE CONSIDERED
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8-15-05

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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) FIS920030371US1		Application Number 10/708,378	
				Applicant(s) Zhu, et al.			
				Filing Date 2-27-04		Group Art Unit 2818	
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Saki			
		5,989,978	11-23-99	Peidous			
M		6,008,126	12-28-99	Leedy			
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
M		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.					
M		H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.					
EXAMINER <i>MJM ✓ M</i>				DATE CONSIDERED <i>8-15-05</i>			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)	Application Number
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
NJ		6,025,280	2-15-00	Brady, et al.			
		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
NJ		6,107,143	8-22-00	Park, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

NJ		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.
NJ		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

EXAMINER	<i>M. Johnson</i>	DATE CONSIDERED
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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional) PIS920030371US1	Application Number 10/708,378
Applicant(s) Zhu, et al.	
Filing Date 2-27-04	Group Art Unit 2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Wu		6,117,722	9-12-00	Wuu, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
PL		6,228,694	5-8-01	Doyle, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REP	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

DATE CONSIDERED

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
N		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
N		6,274,444	8-14-01	Wang			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
W		6,361,885	3-26-02	Chou			

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	<i>Nem</i> ✓ <i>M</i>	DATE CONSIDERED
		<i>5-12-05</i>

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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) FIS920030371US1	Application Number 10/708,378
				Applicant(s) Zhu, et al.	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PILING DATE IF APPROPRIATE
<i>MW</i>		6,362,082	3-26-02	Doyle, et al.			
<i>MW</i>		6,368,931	4-9-02	Kuhn, et al.			
<i>MW</i>		6,403,486	6-11-02	Lou			
<i>MW</i>		6,403,975	6-11-02	Brunner, et al.			
<i>MW</i>		6,406,973	6-18-02	Lee			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS *(Including Author, Tide, Date, Pertinent Pages, Etc.)*

EXAMINER	<i>M. Hu</i>	DATE CONSIDERED	<i>5-12-05</i>
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional)		Application Number	
				FIS920030371US1		10/708,378	
				Applicant(s)			
				Zhu, et al.			
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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WY		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
WY		6,498,358	12-24-02	Lach, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
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						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>5-12-05</i>			
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U.S. PATENT DOCUMENTS

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NW		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
NW		6,531,369	3-11-03	Ozkan, et al			

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Mm ✓ M

DATE CONSIDERED

5-12-03

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
NW		6,531,740	3-11-03	Bosco, et al.			
I		6,621,392	9-16-03	Volant, et al.			
NW		6,635,506	10-21-03	Volant, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

M. J. M.

DATE CONSIDERED

5-12-05

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